BC636, BC636-16, BC638, BC640, BC640-16

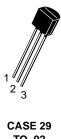
High Current Transistors PNP Silicon



ON Semiconductor

http://onsemi.com

COLLECTOR 2 BASE 1 EMITTER



TO-92 STYLE 14

ORDERING INFORMATION

Device	Package	Shipping
BC636	TO-92	5000 Units/Box
BC636ZL1	TO-92	2000/Ammo Pack
BC636-16ZL1	TO-92	2000/Ammo Pack
BC638	TO-92	5000 Units/Box
BC638ZL1	TO-92	2000/Ammo Pack
BC640	TO-92	5000 Units/Box
BC640ZL1	TO-92	2000/Ammo Pack
BC640–16	TO-92	5000 Units/Box

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC636 BC638 BC640	VCEO	-45 -60 -80	Vdc
Collector-Base Voltage BC636 BC638 BC640	V _{CBO}	-45 -60 -80	Vdc
Emitter-Base Voltage	VEBO	-5.0	Vdc
Collector Current — Continuous	IC	-0.5	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	TJ, Tstg	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	R _θ JC	83.3	°C/W

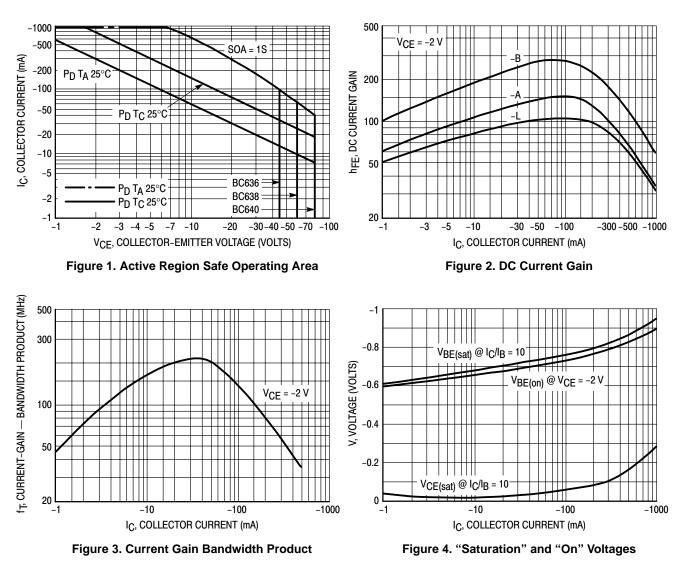
BC636, BC636-16, BC638, BC640, BC640-16

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•		•
Collector–Emitter Breakdown Voltage ($I_C = -10$ mAdc, $I_B = 0$)	BC636 BC638 BC640	V(BR)CEO	-45 -60 -80			Vdc
Collector–Base Breakdown Voltage ($I_C = -100 \ \mu Adc$, $I_E = 0$)	BC636 BC638 BC640	V _(BR) CBO	-45 -60 -80			Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \ \mu Adc, I_C = 0$)		V(BR)EBO	-5.0	—	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -30 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}C)$		Сво	_		-100 -10	nAdc μAdc
ON CHARACTERISTICS (1)						
DC Current Gain (I _C = -5.0 mAdc, V _{CE} = -2.0 Vdc) (I _C = -150 mAdc, V _{CE} = -2.0 Vdc) (I _C = -500 mA, V _{CE} = -2.0 V)	BC636 BC636–16 BC638 BC640 BC640–16	hfe	25 40 100 40 40 100 25		 250 160 160 250 	_
Collector–Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)		V _{CE(sat)}	_	0.25 0.5	-0.5 	Vdc
Base–Emitter On Voltage (I _C = -500 mAdc, V _{CE} = -2.0 Vdc)		V _{BE(on)}	—	—	-1.0	Vdc
DYNAMIC CHARACTERISTICS						
Current–Gain — Bandwidth Product ($I_C = -50$ mAdc, $V_{CE} = -2.0$ Vdc, f = 100 MHz)		fT	_	150	—	MHz
Output Capacitance ($V_{CB} = -10$ Vdc, $I_E = 0$, f = 1.0 MHz)		C _{ob}	_	9.0	—	pF
Input Capacitance (V _{EB} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ib}		110	_	pF

1. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle 2.0%.

BC636, BC636–16, BC638, BC640, BC640–16



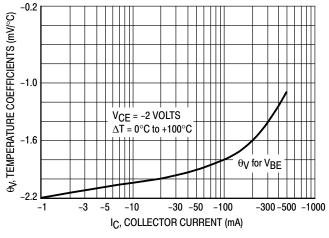
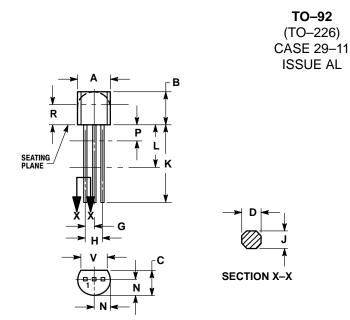


Figure 5. Temperature Coefficients

BC636, BC636-16, BC638, BC640, BC640-16

PACKAGE DIMENSIONS



N	\cap	ΓF	S-

DIMENSIONING AND TOLERANCING PER ANSI 1.

2.

VI14.5M, 1982. CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R 3 IS UNCONTROLLED.

LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE

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